



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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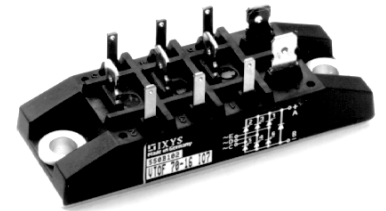
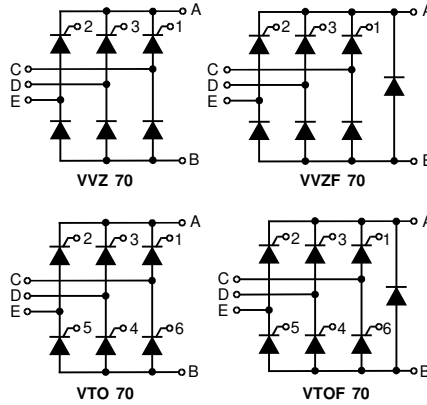


Three Phase Rectifier Bridge

$I_{dAV} = 70 \text{ A}$
 $V_{RRM} = 800-1600 \text{ V}$

Preliminary data

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
800	800	xxx 70-08io7
1200	1200	xxx 70-12io7
1400	1400	xxx 70-14io7
1600	1600	xxx 70-16io7
xxx = type		



Symbol	Test Conditions	Maximum Ratings	
I_{dAV} ①	$T_C = 85^\circ\text{C}$, module	70	A
I_{dAVM} ①	module	70	A
I_{FRMS} , I_{TRMS}	per leg	36	A
I_{FSM} , I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0 \text{ V}$	$t = 10 \text{ ms}$ (50 Hz), sine	550 A
		$t = 8.3 \text{ ms}$ (60 Hz), sine	600 A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0 \text{ V}$	$t = 10 \text{ ms}$ (50 Hz), sine	1520 A ² s
		$t = 8.3 \text{ ms}$ (60 Hz), sine	1520 A ² s
$(di/dt)_{cr}$	$T_{VJ} = 125^\circ\text{C}$ $f = 50 \text{ Hz}$, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$, $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	repetitive, $I_T = 50 \text{ A}$	150 A/ μs
		non repetitive, $I_T = 1/2 \cdot I_{dAV}$	500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)		1000 V/ μs
V_{RGM}			10 V
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30 \mu\text{s}$	$\leq 10 \text{ W}$
		$t_p = 500 \mu\text{s}$	$\leq 5 \text{ W}$
		$t_p = 10 \text{ ms}$	$\leq 1 \text{ W}$
P_{GAVM}			0.5 W
T_{VJ}			-40...+125 °C
T_{VJM}			125 °C
T_{stg}			-40...+125 °C
V_{ISOL}	50/60 Hz, RMS	$t = 1 \text{ min}$	2500 V~
	$I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ s}$	3000 V~
M_d	Mounting torque (M5) (10-32 UNF)		$5 \pm 15 \%$ Nm
			$44 \pm 15 \%$ lb.in.
Weight			50 g

Features

- Package with copper base plate
- Isolation voltage 3000 V~
- Planar passivated chips
- Low forward voltage drop
- 1/4" fast-on power terminals

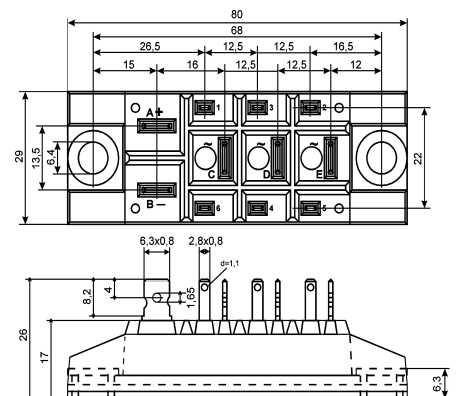
Applications

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- Small and light weight

Dimensions in mm (1 mm = 0.0394")



Data according to IEC 60747 refer to a single diode/thyristor unless otherwise stated

① for resistive load at bridge output. IXYS reserves the right to change limits, test conditions and dimensions.

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Symbol	Test Conditions	Characteristic Values	
I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	\leq	5 mA
V_T	$I_T = 80 \text{ A}; T_{VJ} = 25^\circ\text{C}$	\leq	1.64 V
V_{T0}	For power-loss calculations only		0.85 V
r_T			11 m Ω
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	\leq	1.5 V
	$T_{VJ} = -40^\circ\text{C}$	\leq	1.6 V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	\leq	100 mA
	$T_{VJ} = -40^\circ\text{C}$	\leq	200 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	\leq	0.2 V
I_{GD}		\leq	5 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	\leq	450 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	\leq	200 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	\leq	2 μs
t_q	$T_{VJ} = T_{VJM}; I_T = 20 \text{ A}, t_p = 200 \mu\text{s}; di/dt = -10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 15 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ.	250 μs
R_{thJC}	per thyristor / Diode; DC		0.9 K/W
	per module		0.15 K/W
R_{thJH}	per thyristor / Diode; DC		1.1 K/W
	per module		0.157 K/W
d_s	Creeping distance on surface		16.1 mm
d_A	Creepage distance in air		7.5 mm
a	Max. allowable acceleration		50 m/s ²